

On page 1, line 15, has been deleted.

On page 3, line 6, has been amended to read:

**Brief Summary of the Invention.**

On page 4, line 21, has been amended to read:

A fifth perspective of the present invention provides a method for manufacturing a semiconductor wafer. The method includes performing polishing using a table having a polishing surface for polishing a semiconductor wafer held by a wafer holding plate of a wafer polishing apparatus. The table includes a plurality of superimposed bases, each base being formed from silicide ceramic or carbide ceramic. At least one of the bases has a fluid passage formed in its superimposition interface. The polishing step includes the steps of rotating the semiconductor wafer, and contacting the semiconductor wafer with the polishing surface of the table while circulating coolant water in the fluid passage.

On page 5, line 1, has been amended to read:

A sixth perspective of the present invention is a method for manufacturing a table having a polishing surface for polishing a semiconductor wafer held by a wafer holding plate of a wafer polishing apparatus. The method includes the steps of arranging a foil-like brazing filler between a plurality of bases, each having a groove formed in its surface and each formed from a silicon carbide sinter, and heating each of the bases to braze the bases